

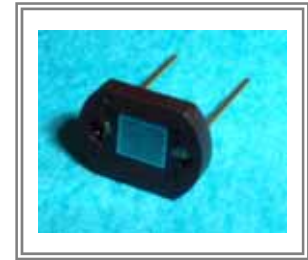
Silicon Photo Diodes

Model No. SD-7BAF

Optoelectronic device

Features

- Sensitive to the visible light only: $\lambda_p=560\text{nm}$
- Suitable for EE cameras, exposure meters, and others
- High reliability



Absolute Maximum Ratings

Ta = 25

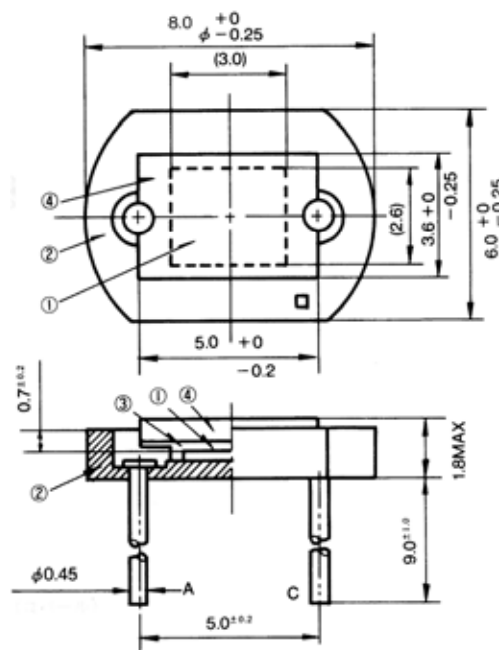
Parameter	Symbol	Value	Unit
DC Reverse Voltage	V_R	20	V
Operating Temperature	Topr	-20 ~ +60	
Storage Temperature	Tstg	-25 ~ +80	

Electro-optical Characteristics

Ta = 25

Parameter	Symbol	MIN	TYP	MAX	Unit	Condition
Sensitive Range	λ	350		730	nm	Equivalent energy
Peak sensitive wavelength	λ_p		560		nm	Equivalent energy
Short Circuit Current	Isc	0.5			μA	100Lx
Dark current	Id			30	pA	$V_R=1\text{V}$. RH 65%
Shortcircuit current temp. coefficient	β_T		--		%/	100Lx
Dark current temp. coefficient	α_T		--		Times/10	$V_R=1\text{V}$. RH 65%
Terminal capacitance	C_T		600		pF	$V_R=0\text{V}$, f=1MHz
Spectral sensitivity	IR		--	--	%	$\lambda=700\text{nm}$, Isc ratio

External Dimension (unit: mm)



Anode
Cathode
Resin
Filter

Active area: 5.92mm^2

Package

Ceramic